



K. Memory (Design & Process Technology) 분과

2019년 2월 15일(금), 15:30-17:00

Room A (아라홀, 2층)

[FA3-K] Memory Technologies

좌장: 권용우 교수(홍익대학교), 손용훈 수석(삼성전자)

<p>FA3-K-1 15:30-16:00</p>	<p>[초청] Spin Torque Devices for Future Non-volatile Memories Kon-Woo Kwon <i>Department of Computer Engineering, Hongik University</i></p>
<p>FA3-K-2 16:00-16:15</p>	<p>Analytical Current-Voltage Model for Gate-All-Around Transistor with Poly-Silicon Channel Yoongeun Seon, Jaehun Kim, Jaehyun Lee, and Jongwook Jeon <i>Department of Electrical and Electronic Engineering, Konkuk University</i></p>
<p>FA3-K-3 16:15-16:30</p>	<p>The Semiconductors Recycling is the Gold Mining in Urban Area Tae Kyung Kwon, Young Ho Kwon, and Monyo John Wonder Mensah Kwaku <i>Department of Product Marketing, MicroMicroChips Ilc, USA</i></p>
<p>FA3-K-4 16:30-16:45</p>	<p>Effect of Diammonium Hydrogen Phosphate on Selectivity Between Si₃N₄ and Poly-Si High Selectivity CMP Slurry Hae-Won Nam¹, Sang-Su Yun¹, Gi-Ppeum Jeong¹, Jin-Hyung Park², and Jea-Gun Park¹ <i>¹Advanced Semiconductor Materials and Devices Development Center, Hanyang University, ²UB Materials Inc.</i></p>
<p>FA3-K-5 16:45-17:00</p>	<p>Flash Memory Operation with C-Axis Aligned Crystalline IGZO (CAAC-IGZO) Thin Film Channel Material Prepared by Metal-Induced Crystallization Hoonhee Han¹, Hyungju Soel², Jae Kyeong Jeong², and Changhwan Choi¹ <i>¹Division of Materials Science and Engineering, Hanyang University, ²Department of Electronic Engineering, Hanyang University</i></p>